

GL358

NPN SILICON PLANAR HIGH CURRENT TRANSISTOR

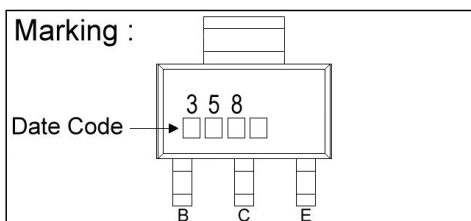
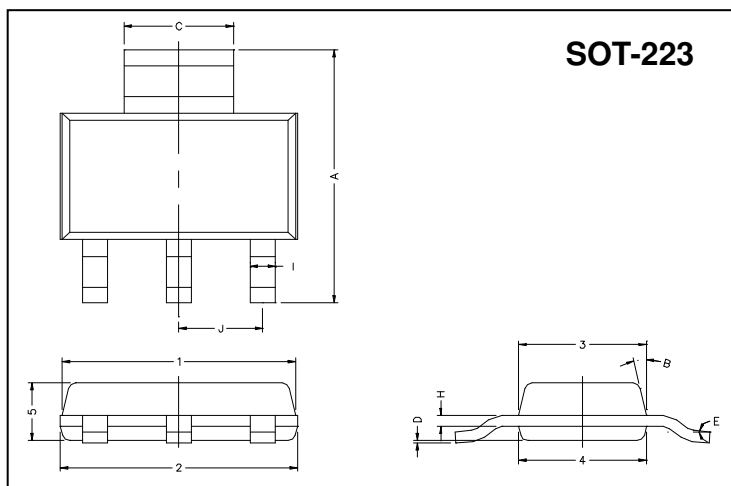
Description

The GL358 is designed for general purpose switching and amplifier applications.

Features

- 6 Amps continuous current, up to 10Amps peak current
- Excellent gain characteristic specified up to 10Amps
- Very low saturation voltages

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	200	V
Collector to Emitter Voltage	VCEO	100	V
Emitter to Base Voltage	VEBO	6	V
Collector Current (DC)	IC	6	A
Collector Current (Pulse)	Ic	10	A
Total Power Dissipation	Pd	3	W

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 4 square inch minimum.

Electrical Characteristics (Ta = 25°C, unless otherwise stated)

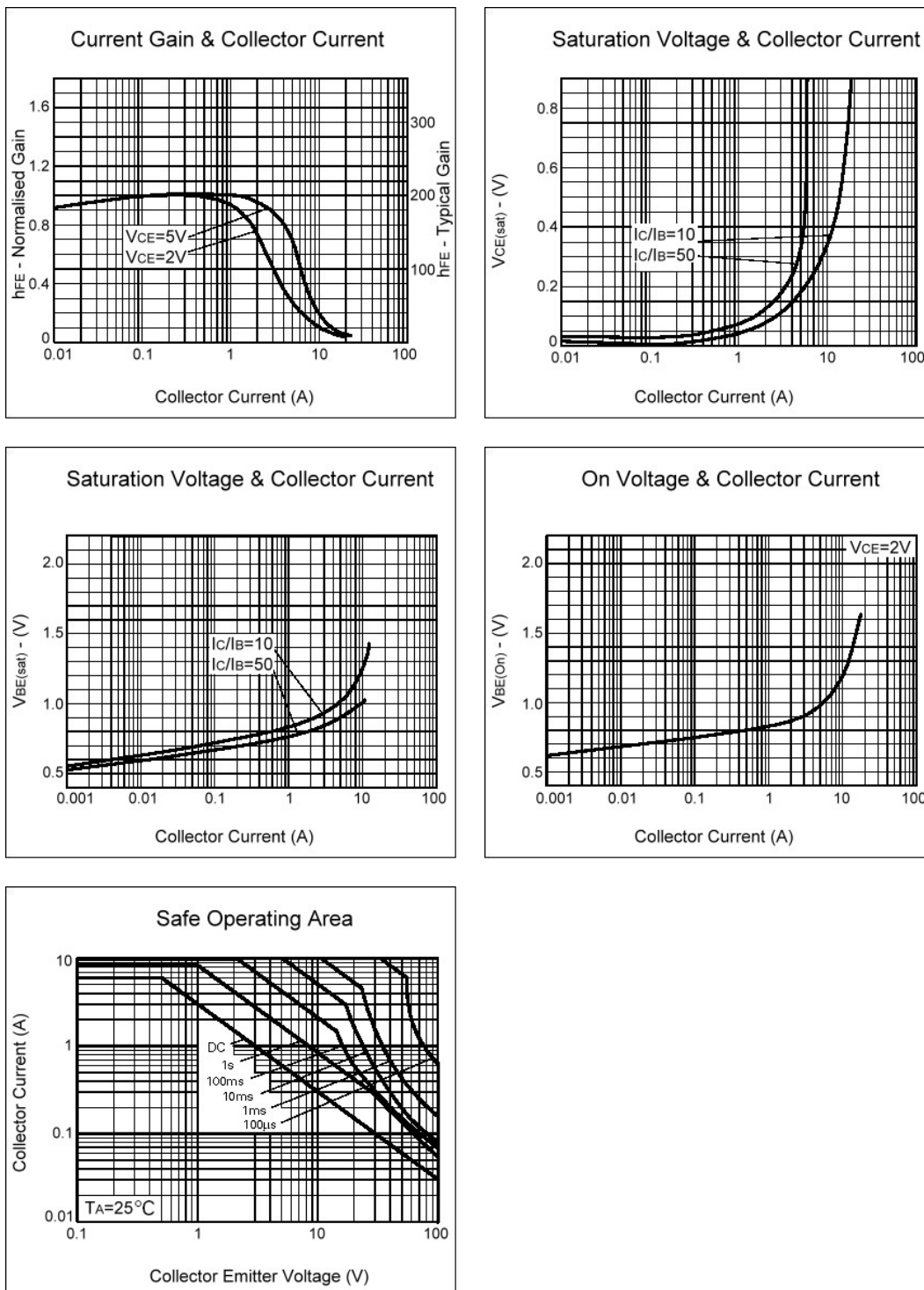
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	200	-	-	V	IC=100uA, IE=0
*BVCEO	100	-	-	V	IC=10mA, IB=0
BVEBO	6	-	-	V	IE=100uA, IC=0
ICBO	-	-	10	nA	VCB=150V, IE=0
ICES	-	-	50	nA	VCE=100V
IEBO	-	-	10	nA	VEB=6V, IC=0
*VCE(sat)1	-	-	50	mV	IC=100mA, IB=5mA
*VCE(sat)2	-	-	150	mV	IC=2A, IB=100mA
*VCE(sat)3	-	-	340	mV	IC=5A, IB=500mA
*VBE(sat)	-	-	1.25	V	IC=5A, IB=500mA
*VBE(on)	-	-	1.10	V	VCE=2V, IC=5A
*hFE1	100	-	-		VCE=2V, IC=10mA
*hFE2	100	200	300		VCE=2V, IC=2A
*hFE3	50	-	-		VCE=2V, IC=4A
*hFE4	20	-	-		VCE=2V, IC=10A
fT	-	130	-	MHz	VCE=10V, IC=100mA, f=50MHz
Cob	-	35	-	pF	VCB=10V, IE=0, f=1MHz

ton	-	55	-	ns	V _{CC} =10V, I _C =1A, I _{B1} =I _{B2} =100mA
toff	-	1650	-		

*Measured under pulse condition. Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Spice parameter data is available upon request for this device.

Characteristics Curve



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